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Kind regards,

Team Nexperia

74LV132

Quad 2-input NAND Schmitt trigger

Rev. 6 — 9 December 2015

Product data sheet

1. General description

The 74LV132 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC132 and 74HCT132.

The 74LV132 contains four 2-input NAND gates which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The gate switches at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H .

2. Features and benefits

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3. Applications

- Wave and pulse shapers for highly noisy environments
- Astable multivibrators
- Monostable multivibrators



4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LV132D	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV132DB	−40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV132PW	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV132BQ	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

5. Functional diagram

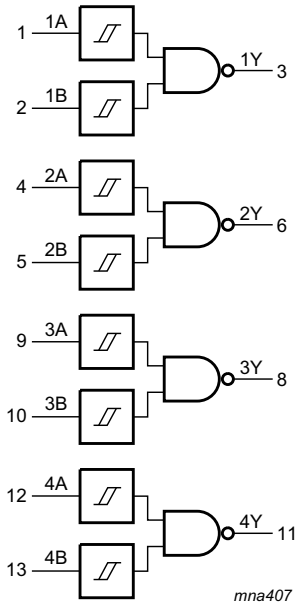


Fig 1. Logic symbol

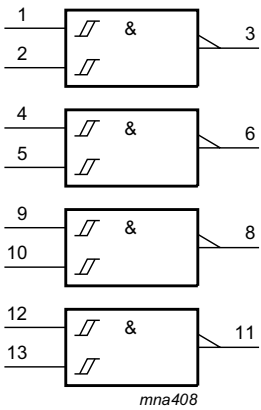


Fig 2. IEC logic symbol

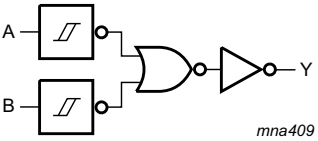
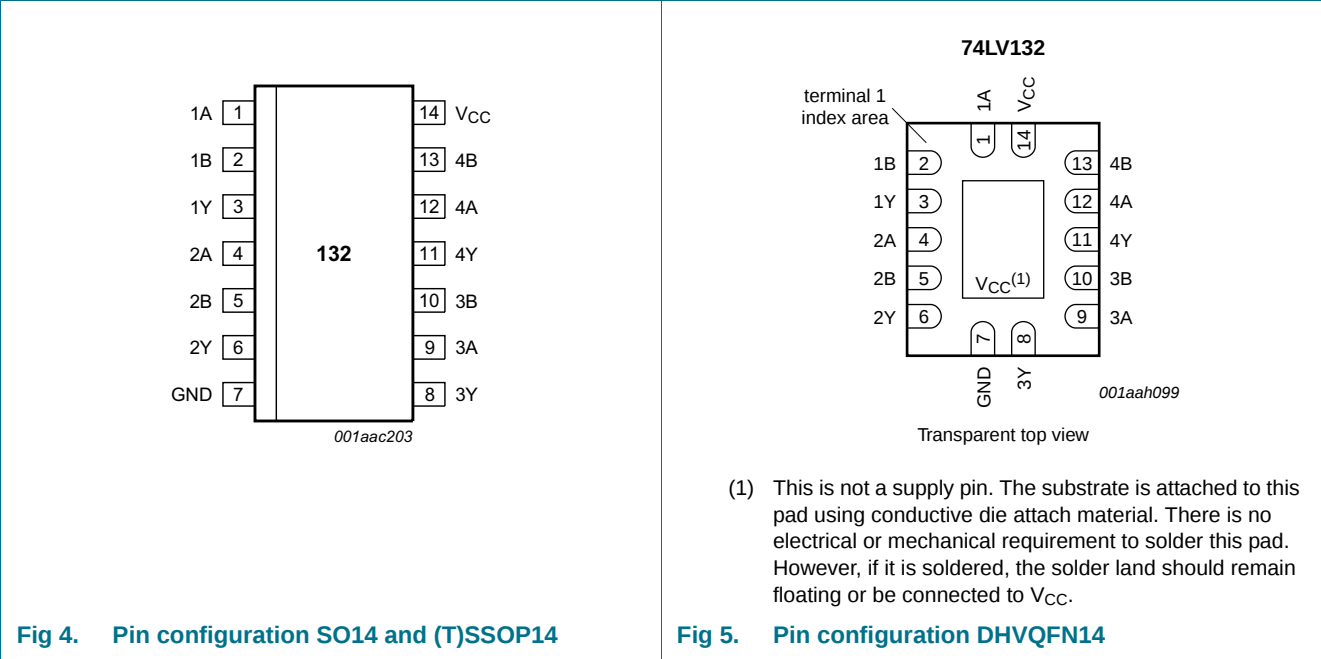


Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 4, 9, 12	data input
1B to 4B	2, 5, 10, 13	data input
1Y to 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
VCC	14	supply voltage

7. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ [1]	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ [1]	-	± 50	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$			
		SO14 package [2]	-	500	mW
		(T)SSOP14 package [3]	-	500	mW
		DHVQFN14 package [4]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage [1]		1.0	3.3	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$, but LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

10. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T–}						
		I _O = –100 µA; V _{CC} = 1.2 V	-	1.2	-	-	-	V
		I _O = –100 µA; V _{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I _O = –100 µA; V _{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I _O = –100 µA; V _{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I _O = –100 µA; V _{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I _O = –6 mA; V _{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I _O = –12 mA; V _{CC} = 4.5 V	3.6	4.2	-	3.5	-	V
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T–}						
		I _O = 100 µA; V _{CC} = 1.2 V	-	0	-	-	-	V
		I _O = 100 µA; V _{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	-	40	µA
ΔI _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	µA
C _I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

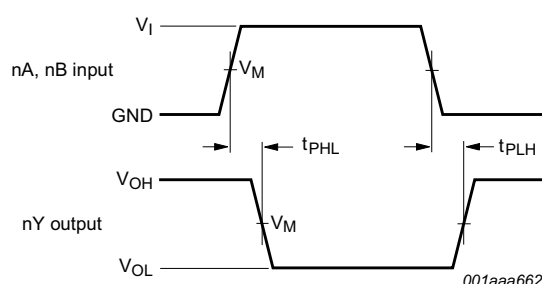
11. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, nB to nY; see Figure 6 ^[2]						
		$V_{CC} = 1.2\text{ V}$	-	65	-	-	-	ns
		$V_{CC} = 2.0\text{ V}$	-	18	34	-	43	ns
		$V_{CC} = 2.7\text{ V}$	-	15	24	-	30	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}; C_L = 15\text{ pF}$ ^[3]	-	10	-	-	-	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ ^[3]	-	12	20	-	25	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ ^[3]	-	9.0	14	-	17	ns
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}; f_i = 1\text{ MHz}; V_i = \text{GND to }V_{CC}$ ^[4]	-	24	-	-	-	pF

- [1] All typical values are measured at $T_{amb} = 25\text{ °C}$.
 [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
 [3] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3\text{ V}$ and $V_{CC} = 5.0\text{ V}$).
 [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz, f_o = output frequency in MHz
 C_L = output load capacitance in pF
 V_{CC} = supply voltage in V
 N = number of inputs switching
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

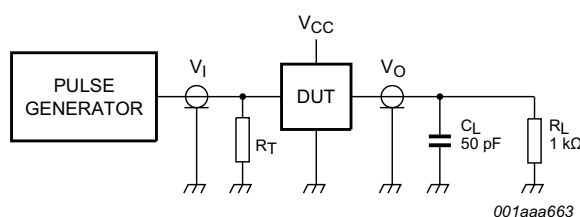


Measurement points are given in Table 8.
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input	
V_{CC}	V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

13. Transfer characteristics

Table 10. Transfer characteristics

$GND = 0$ V; For test circuit see [Figure 7](#).

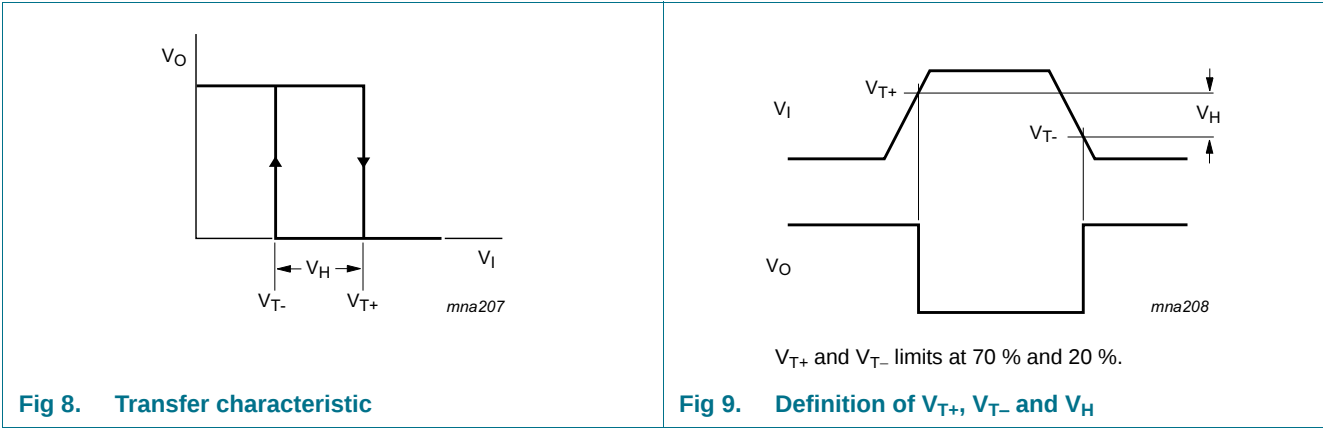
Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 6						
		$V_{CC} = 1.2$ V	-	0.70	-	-	-	V
		$V_{CC} = 2.0$ V	0.8	1.10	1.4	0.8	1.4	V
		$V_{CC} = 2.7$ V	1.0	1.45	2.0	1.0	2.0	V
		$V_{CC} = 3.0$ V	1.2	1.60	2.2	1.2	2.2	V
		$V_{CC} = 3.6$ V	1.5	1.95	2.4	1.5	2.4	V
		$V_{CC} = 4.5$ V	1.7	2.50	3.2	1.7	3.2	V
		$V_{CC} = 5.5$ V	2.1	3.00	3.9	2.1	3.9	V

Table 10. Transfer characteristics ...continued
GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{T−}	negative-going threshold voltage	see Figure 6						
		V _{CC} = 1.2 V	-	0.34	-	-	-	V
		V _{CC} = 2.0 V	0.3	0.65	0.9	0.3	0.9	V
		V _{CC} = 2.7 V	0.4	0.90	1.4	0.4	1.4	V
		V _{CC} = 3.0 V	0.6	1.05	1.5	0.6	1.5	V
		V _{CC} = 3.6 V	0.8	1.30	1.8	0.8	1.8	V
		V _{CC} = 4.5 V	0.9	1.60	2.0	0.9	2.0	V
V _H	hysteresis voltage	(V _{T+} − V _{T−}); see Figure 6						
		V _{CC} = 1.2 V	-	0.3	-	-	-	V
		V _{CC} = 2.0 V	0.2	0.55	0.8	0.2	0.8	V
		V _{CC} = 2.7 V	0.3	0.60	1.1	0.3	1.1	V
		V _{CC} = 3.0 V	0.4	0.65	1.2	0.4	1.2	V
		V _{CC} = 3.6 V	0.4	0.70	1.2	0.4	1.2	V
		V _{CC} = 4.5 V	0.4	0.80	1.4	0.4	1.4	V
		V _{CC} = 5.5 V	0.6	1.00	1.5	0.6	1.5	V

[1] All typical values are measured at T_{amb} = 25 °C.

14. Waveforms transfer characteristics



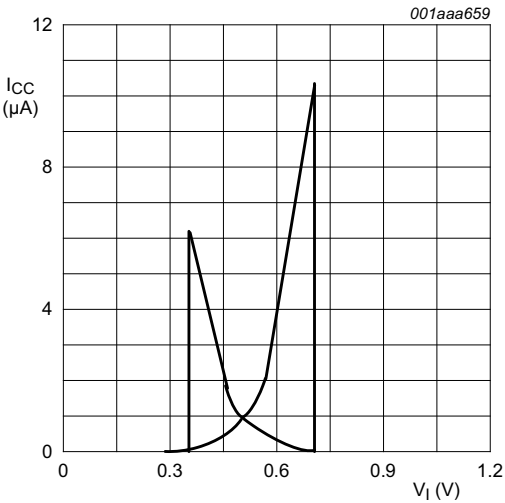


Fig 10. Typical 74LV132 transfer characteristics

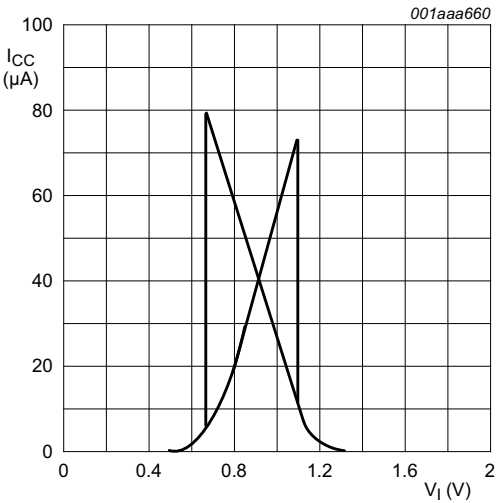


Fig 11. Typical 74LV132 transfer characteristics

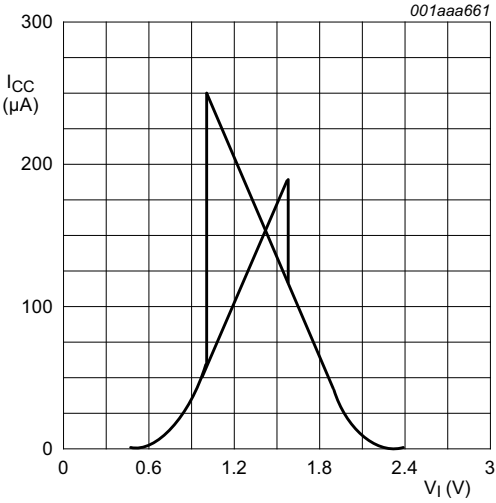


Fig 12. Typical 74LV132 transfer characteristics

15. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

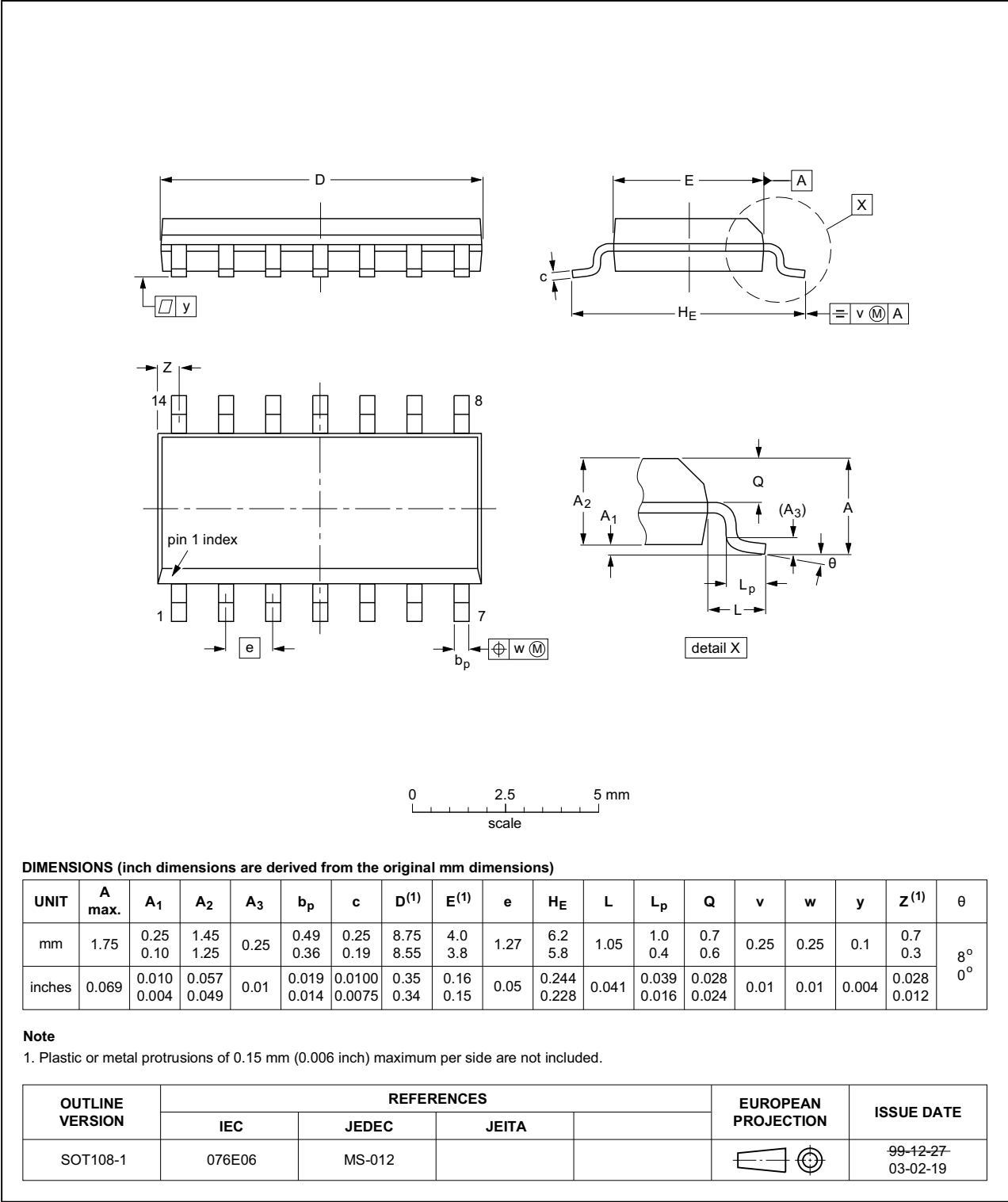


Fig 13. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

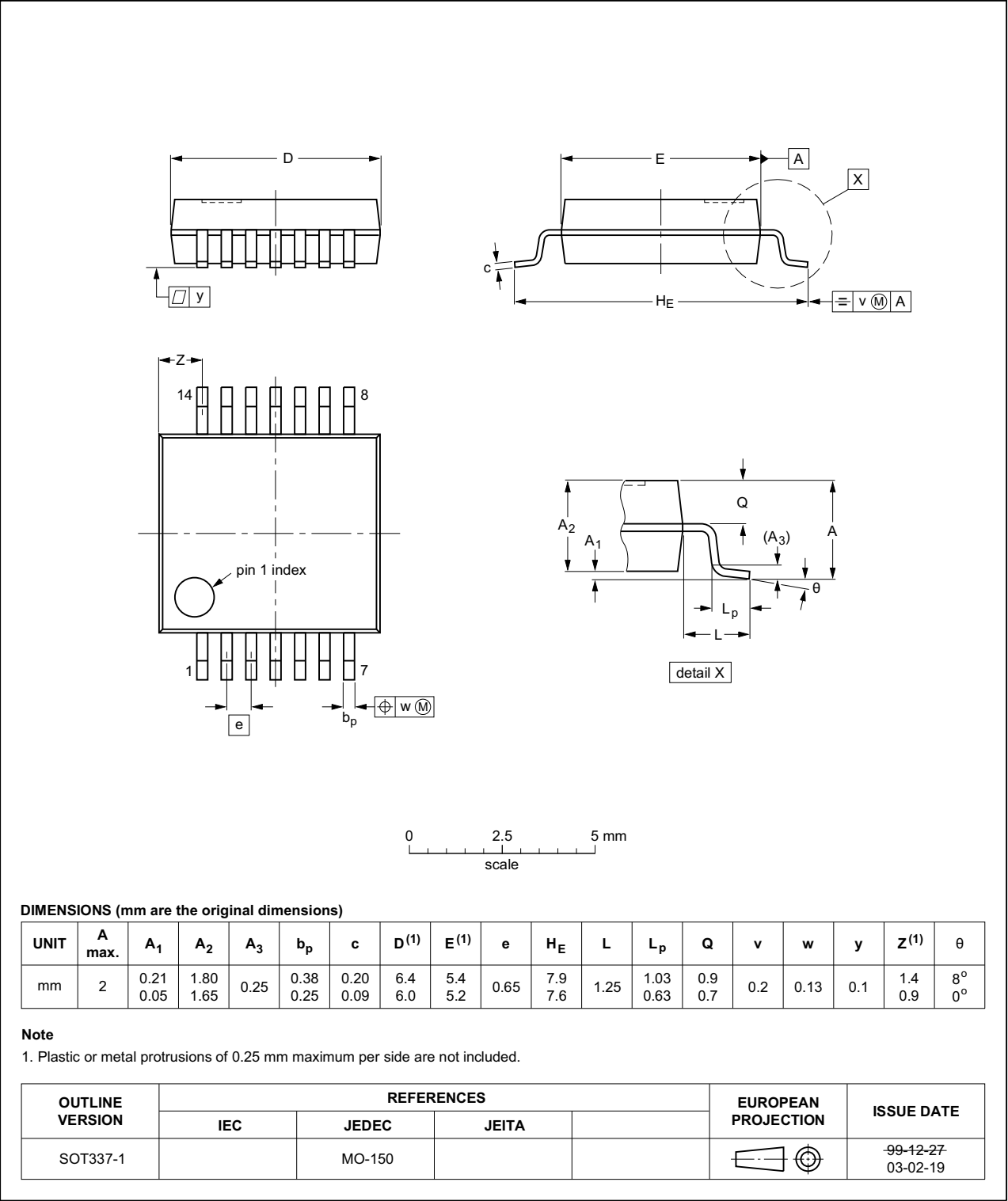


Fig 14. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

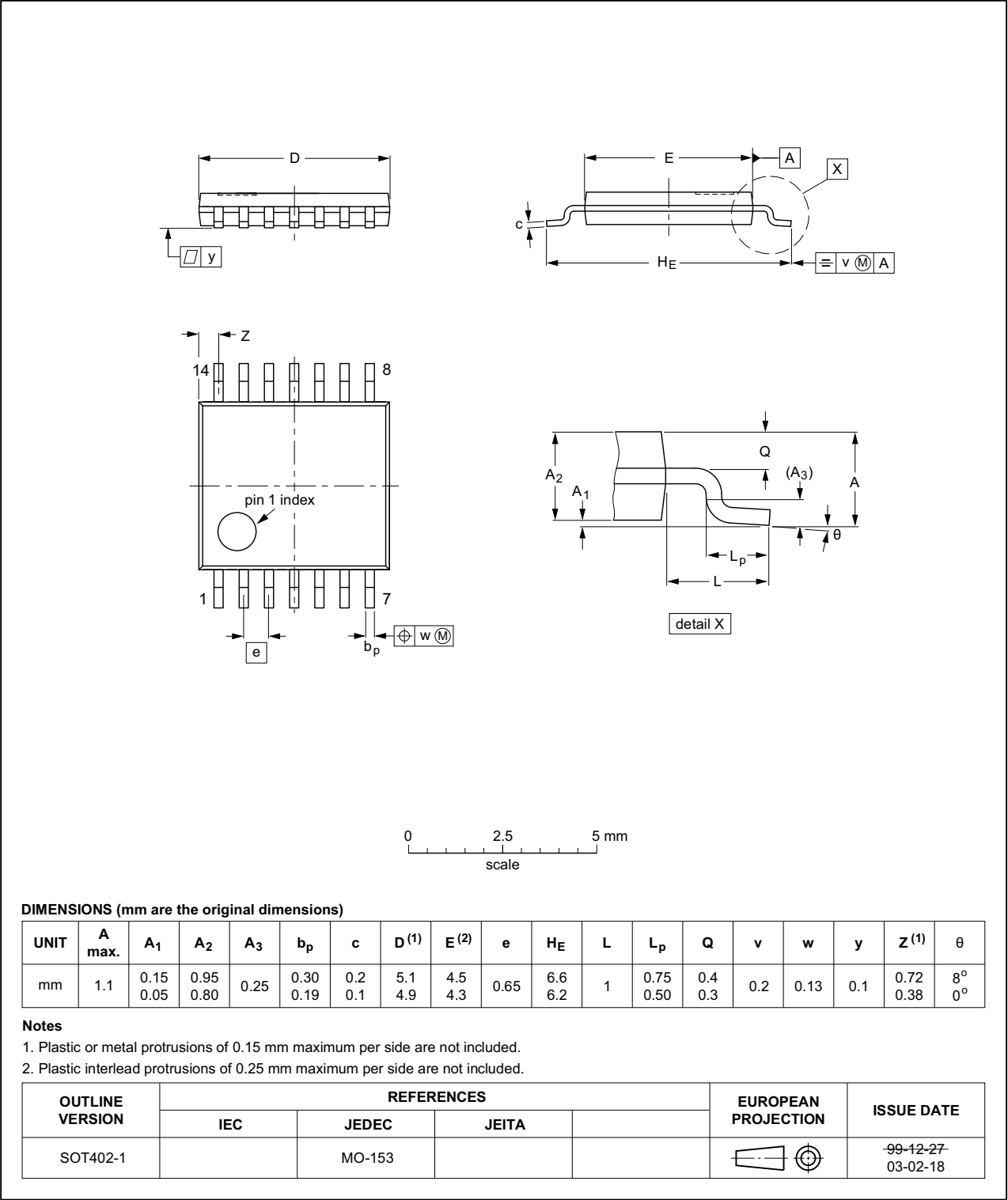


Fig 15. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

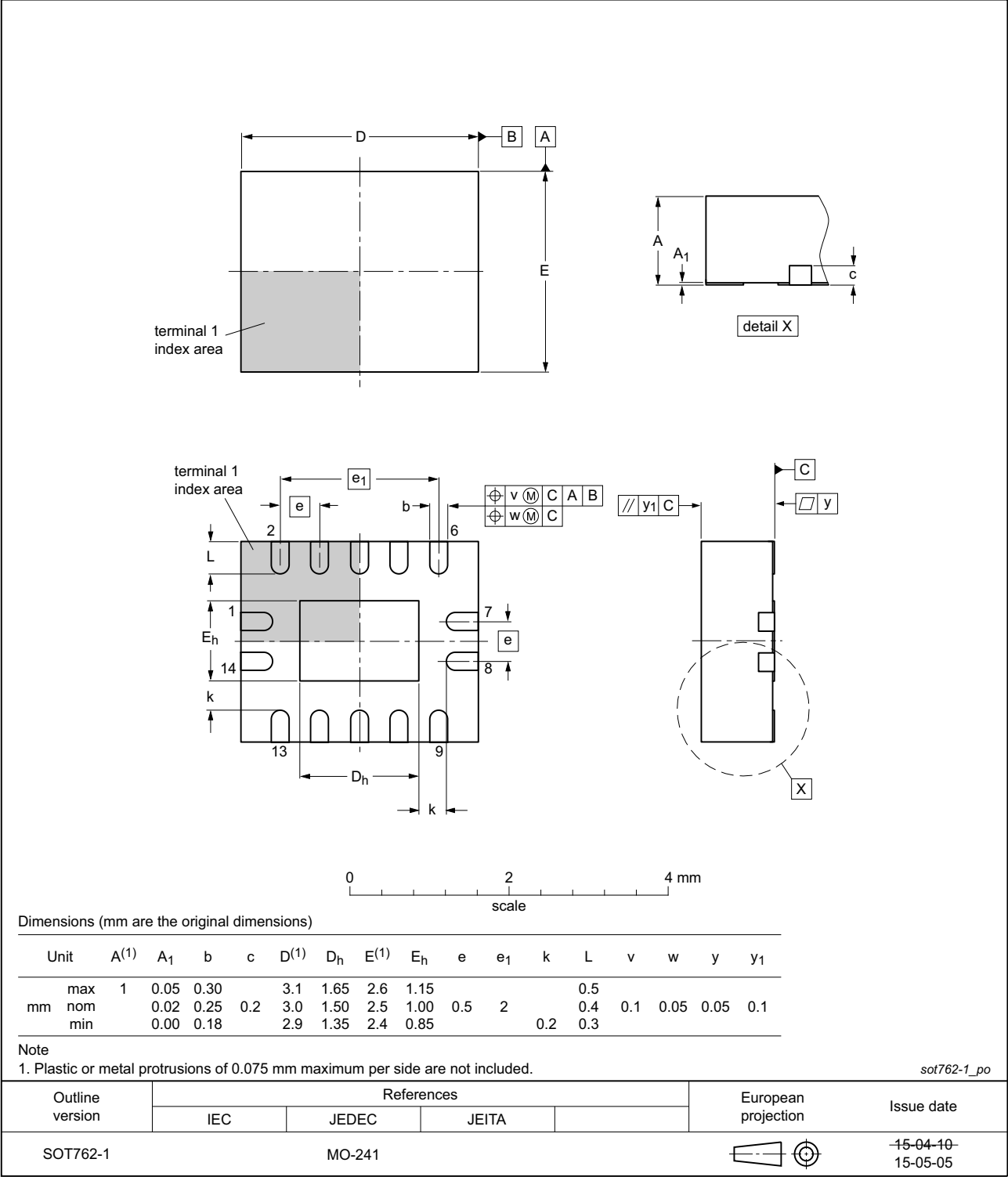


Fig 16. Package outline SOT762-1 (DHVQFN14)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV132 v.6	20151209	Product data sheet	-	74LV132 v.5
Modifications:	• Type number 74LV132N (SOT27-1) removed.			
74LV132 v.5	20090702	Product data sheet	-	74LV132 v.4
Modifications:	• Table 6 : the conditions for HIGH-level output voltage and LOW-level output voltage have been changed.			
74LV132 v.4	20071112	Product data sheet	-	74LV132 v.3
74LV132 v.3	20040415	Product specification	-	74LV132 v.2
74LV132 v.2	19980428	Product specification	-	74LV132 v.1
74LV132 v.1	19970204	Product specification	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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19. Contact information

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20. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Ordering information	2
5	Functional diagram	2
6	Pinning information	3
6.1	Pinning	3
6.2	Pin description	3
7	Functional description	3
8	Limiting values	4
9	Recommended operating conditions	4
10	Static characteristics	5
11	Dynamic characteristics	6
12	Waveforms	6
13	Transfer characteristics	7
14	Waveforms transfer characteristics	8
15	Package outline	10
16	Abbreviations	14
17	Revision history	14
18	Legal information	15
18.1	Data sheet status	15
18.2	Definitions	15
18.3	Disclaimers	15
18.4	Trademarks	16
19	Contact information	16
20	Contents	17

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